

Medium power transistor (−60V, −0.5A)

2SA2088

●Features

- 1) High speed switching.
(Tf : Typ. : 60ns at Ic = −500mA)
- 2) Low saturation voltage, typically
(Typ. : −150mV at Ic = −100mA, Ib = −10mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SC5876

●Applications

Small signal low frequency amplifier
High speed switching

●Structure

PNP Silicon epitaxial planar transistor

●Packaging specifications

Type	Package	Taping
	Code	T106
	Basic ordering unit (pieces)	3000
2SA2088		○

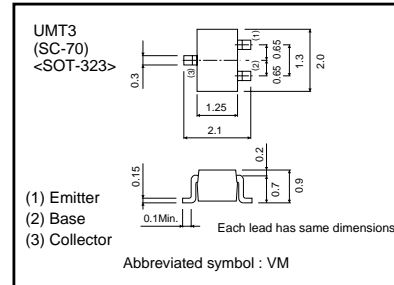
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	−60	V
Collector-emitter voltage	V _{CE0}	−60	V
Emitter-base voltage	V _{EB0}	−6	V
Collector current	DC	I _c	−0.5 A
	Pulsed	I _{cP}	−1.0 A *1
Power dissipation	P _c	200	mW *2
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55 to 150	°C

*1 Pw=10ms

*2 Each terminal mounted on a recommended land

●External dimensions (Unit : mm)



Transistors

●Electrical characteristics (Ta=25°C)

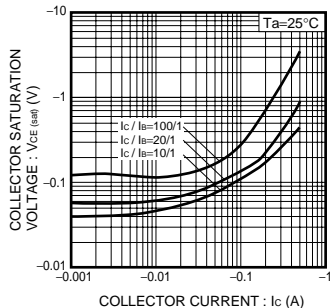
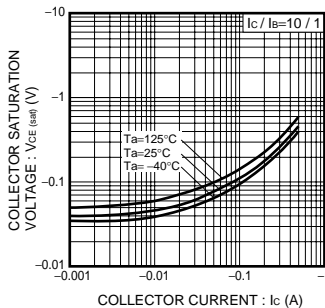
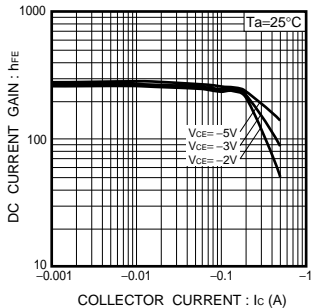
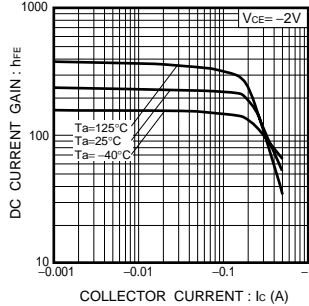
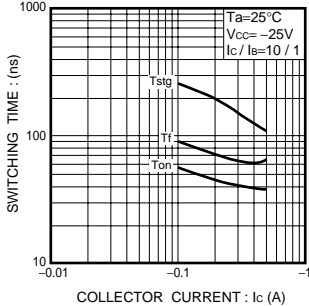
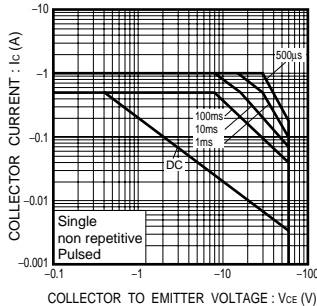
Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	BV _{CEO}	-60	-	-	V	I _c = -1mA
Collector-base breakdown voltage	BV _{CBO}	-60	-	-	V	I _c = -100μA
Emitter-base breakdown voltage	BV _{EBO}	-6	-	-	V	I _E = -100μA
Collector cut-off current	I _{cBO}	-	-	-1.0	μA	V _{CB} = -40V
Emitter cut-off current	I _{EBO}	-	-	-1.0	μA	V _{EB} = -4V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-150	-300	mV	I _c = -100mA I _B = -10mA
DC current gain	h _{FE}	120	-	270	-	V _{CE} = -2V I _c = -50mA
Transition frequency	f _r	-	400	-	MHz	V _{CE} = -10V I _E =100mA f=10MHz
Collector output capacitance	C _{ob}	-	10	-	pF	V _{CB} = -10V I _E =0A f=1MHz
Turn-on time	T _{on}	-	40	-	ns	I _c = -500mA I _{B1} = -50mA I _{B2} =50mA V _{CC} = -25V
Storage time	T _{stg}	-	110	-	ns	
Fall time	T _f	-	60	-	ns	

*1 Non repetitive pulse
*2 See Switching characteristics measurement circuits

●h_{FE} RANK

Q
120-270

●Electrical characteristic curves



Transistors

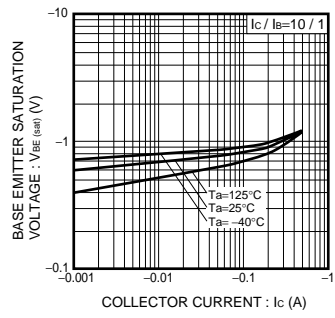


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

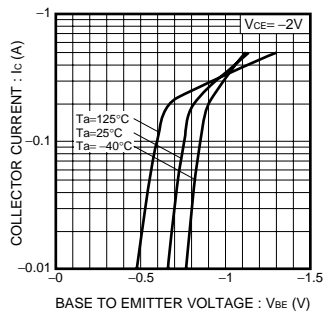


Fig.8 Grounded Emitter Propagation Characteristics

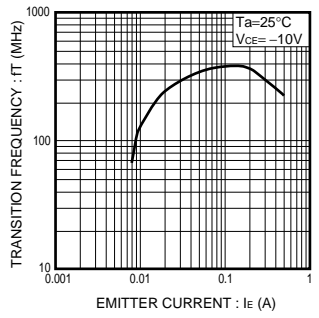


Fig.9 Transition Frequency

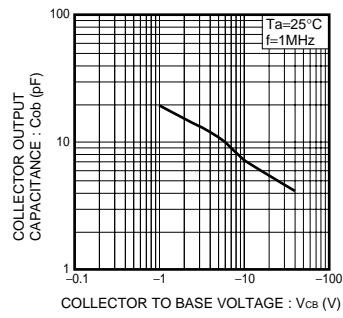
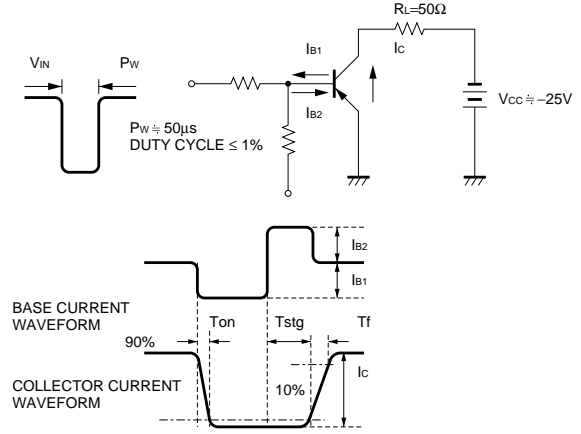


Fig.10 Collector Output Capacitance

● Switching characteristics measurement circuits



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